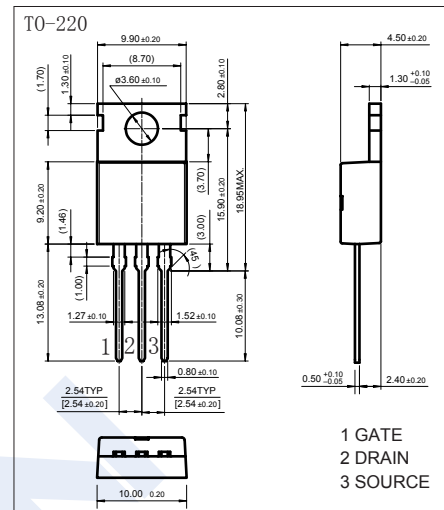
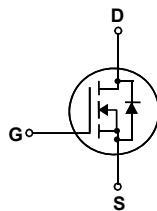


N-Channel Enhancement MOSFET

KX6N70

■ Features

- $V_{DS} (V) = 700V$
- $I_D = 6.0A$ ($V_{GS} = 10V$)
- $R_{DS(ON)} < 1.8 \Omega$ ($V_{GS} = 10V$)
- Low gate charge (typical 16nC)

■ Absolute Maximum Ratings $T_a = 25^\circ C$

Parameter		Symbol	Rating	Unit
Drain-Source Voltage		V_{DS}	700	V
Gate-Source Voltage		V_{GS}	± 30	
Continuous Drain Current	$T_c = 25^\circ C$	I_D	6.0	A
	$T_c = 100^\circ C$		3.6	
Pulsed Drain Current (Note.1)		I_{DM}	24	
Avalanche Current (Note.1)		I_{AR}	6.0	
Repetitive Avalanche Energy (Note.1)		E_{AR}	14.7	mJ
Single Pulsed Avalanche Energy (Note.2)		E_{AS}	150	
Power Dissipation	$T_c = 25^\circ C$	P_D	147	W
	Derate above $25^\circ C$		1.18	W/ $^\circ C$
Peak Diode Recovery dv/dt (Note.3)		dv/dt	4.5	V/ns
Thermal Resistance.Junction- to-Ambient		R_{thJA}	62.5	$^\circ C/W$
Thermal Resistance.Junction- to-Case		R_{thJC}	0.85	
Thermal Resistance.Case-to-Sink Typ		R_{thJS}	0.5	
Maximum lead Temperature for soldering purpose, 1/8 from case for 5 seconds		T_L	300	$^\circ C$
Junction Temperature		T_J	150	
Storage Temperature Range		T_{stg}	-55 to 150	

Note.1: Repetitive Rating :Pulse width limited by maximum junction temperature

Note.2: $L=8mH, I_{AS}=6.0A, V_{DD}=50V, R_G=25\Omega$, Starting $T_J=25^\circ C$

Note.3: $I_{SD} \leq 6.0A, di/dt \leq 200A/\mu s, V_{DD} \leq BV_{DSS}$, Starting $T_J=25^\circ C$

N-Channel Enhancement MOSFET

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■ Electrical Characteristics Ta = 25℃

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	V_{DS}	$I_D=250\mu A$, $V_{GS}=0V$	700			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=700V$, $V_{GS}=0V$			1	μA
		$V_{DS}=560V$, $V_{GS}=0V$, $T_c=125^\circ C$			10	
Gate-Body Leakage Current	I_{GSS}	$V_{DS}=0V$, $V_{GS}=\pm 30V$			± 100	nA
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$, $I_D=250\mu A$	2.0		4.0	V
Static Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS}=10V$, $I_D=3.0A$		1.8	2.3	Ω
Input Capacitance	C_{iss}	$V_{GS}=0V$, $V_{DS}=25V$, $f=1MHz$		650		pF
Output Capacitance	C_{oss}			95		
Reverse Transfer Capacitance	C_{rss}			10		
Total Gate Charge	Q_g	$V_{GS}=10V$, $V_{DS}=560V$, $I_D=6.0A$ (Note.1)		16		nC
Gate Source Charge	Q_{gs}			4.5		
Gate Drain Charge	Q_{gd}			5.0		
Turn-On DelayTime	$t_{d(on)}$	$I_D=6.0A$, $V_{DS}=350V$, $R_{GEN}=25\Omega$ (Note.1)		30		ns
Turn-On Rise Time	t_r			40		
Turn-Off DelayTime	$t_{d(off)}$			80		
Turn-Off Fall Time	t_f			40		
Body Diode Reverse Recovery Time	t_{rr}	$I_S=6.0A$, $di/dt=100A/\mu s$, $V_{GS}=0V$ (Note.1)		280		ns
Body Diode Reverse Recovery Charge	Q_{rr}			2.0		
Maximum Body-Diode Continuous Current	I_S	Maximum Continuous Drain-Source Diode Forward Current			6.0	A
Maximum Pulsed Drain-Source Current	I_{SM}	Maximum Pulsed Drain-Source Diode Forward Current			24	
Diode Forward Voltage	V_{SD}	$I_S=6.0A$, $V_{GS}=0$			1.4	V

Note.1: Pulse Test:Pulse width $\leq 300\mu s$,Duty cycle $\leq 2\%$

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■ Typical Characteristics

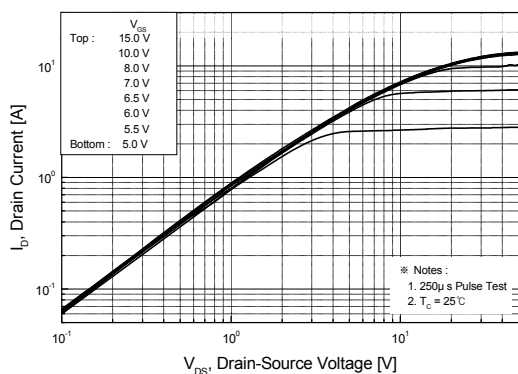


Figure 1. On-Region Characteristics

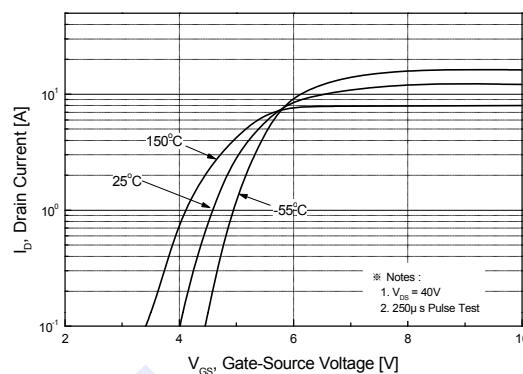


Figure 2. Transfer Characteristics

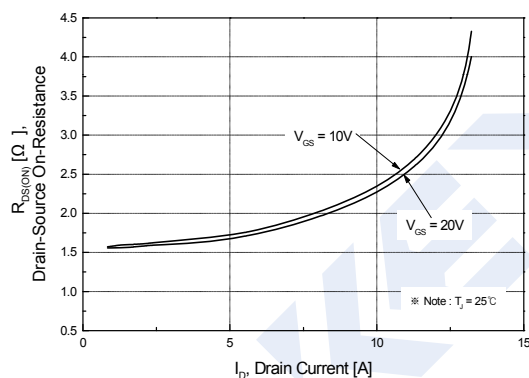


Figure 3. On-Resistance Variation vs Drain Current and Gate Voltage

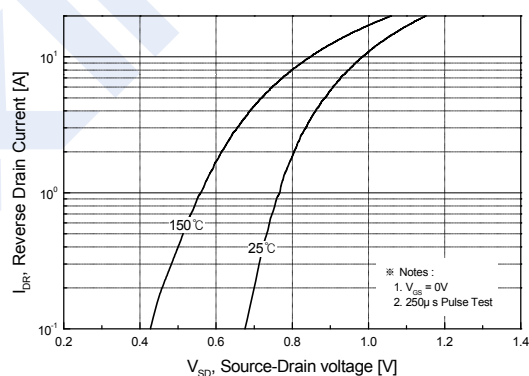


Figure 4. Body Diode Forward Voltage Variation with Source Current and Temperature

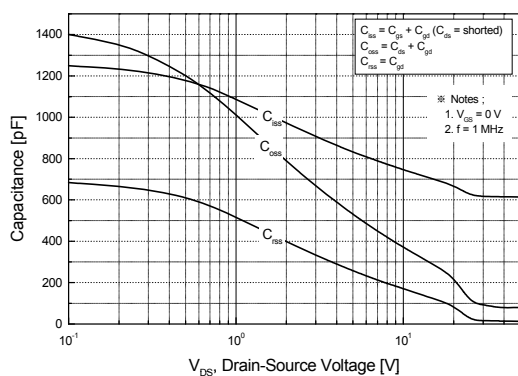


Figure 5. Capacitance Characteristics

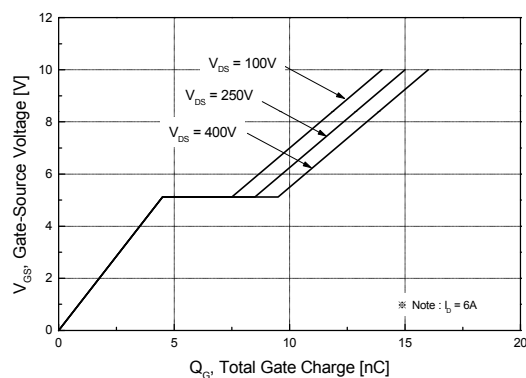


Figure 6. Gate Charge Characteristics

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■ Typical Characteristics

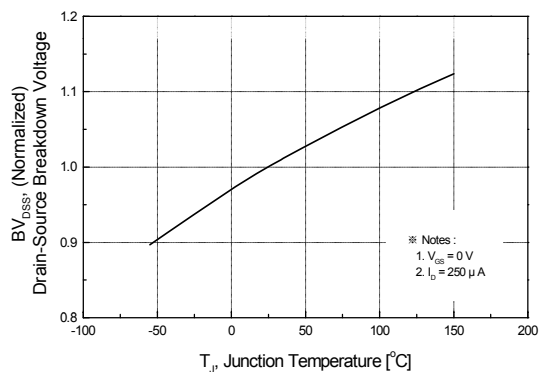


Figure 7. Breakdown Voltage Variation vs Temperature

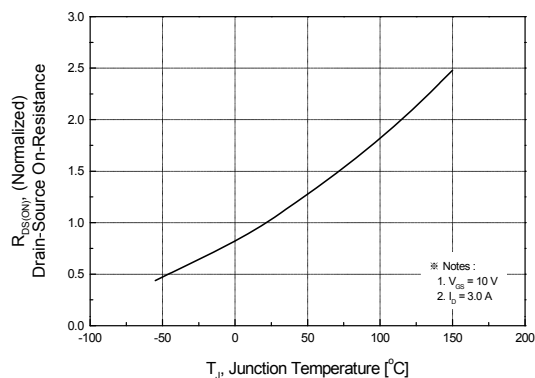


Figure 8. On-Resistance Variation vs Temperature

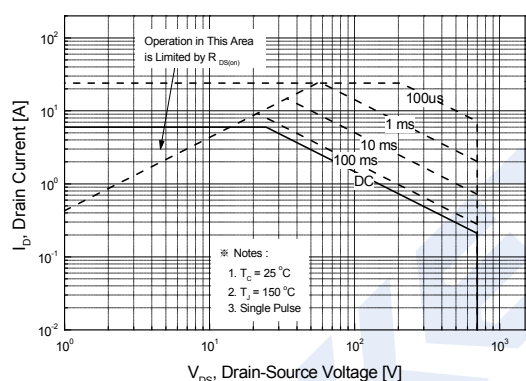


Figure 9. Maximum Safe Operating Area for KX6N70

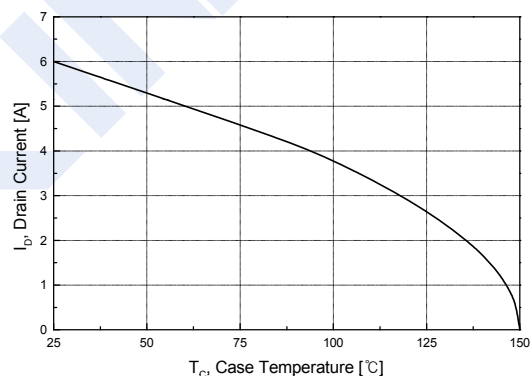


Figure 10. Maximum Drain Current vs Case Temperature

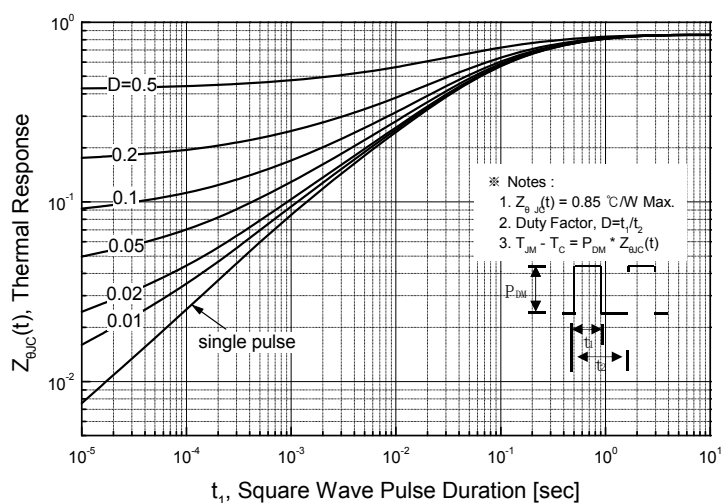


Figure 11. Transient Thermal Response Curve for KX6N70